

MOSFETs Silicon N-Channel MOS

# SSM3K336R

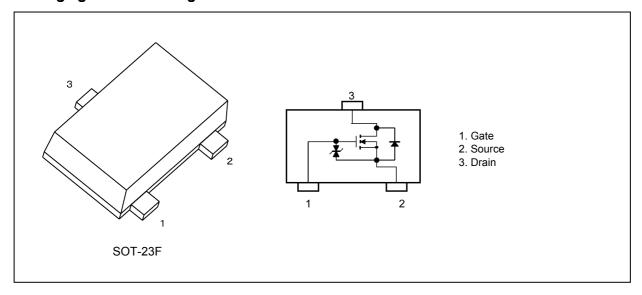
#### 1. Applications

- · Power Management Switches
- · DC-DC Converters

#### 2. Features

- (1) 4.5 V gate drive voltage.
- (2) Low drain-source on-resistance
  - :  $R_{DS(ON)}$  = 95 m $\Omega$  (max) (@ $V_{GS}$  = 10 V)  $R_{DS(ON)}$  = 140 m $\Omega$  (max) (@ $V_{GS}$  = 4.5 V)

## 3. Packaging and Pin Configuration





## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25°C)

|                        | Characteristics |            | Symbol           | Rating     | Unit |
|------------------------|-----------------|------------|------------------|------------|------|
| Drain-source voltage   |                 |            | $V_{DSS}$        | 30         | V    |
| Gate-source voltage    |                 |            | V <sub>GSS</sub> | ±20        |      |
| Drain current (DC)     |                 | (Note 1)   | I <sub>D</sub>   | 3          | Α    |
| Drain current (pulsed) |                 | (Note 1,2) | I <sub>DP</sub>  | 8          |      |
| Power dissipation      |                 | (Note 3)   | P <sub>D</sub>   | 1          | W    |
| Power dissipation      | (t ≤ 10 s)      | (Note 3)   | P <sub>D</sub>   | 2          | W    |
| Channel temperature    |                 |            | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature    |                 |            | T <sub>stg</sub> | -55 to 150 |      |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%
- Note 3: Device mounted on a FR4 board.(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

## 5.1. Static Characteristics (Unless otherwise specified, Ta = 25°C)

| Characteristics                |          | Symbol               | Test Condition                                    | Min | Тур. | Max | Unit |
|--------------------------------|----------|----------------------|---|-----|------|-----|------|
| Gate leakage current           |          | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _   |      | ±10 | μА   |
| Drain cut-off current          |          | I <sub>DSS</sub>     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V     |     |      | 1   |      |
| Drain-source breakdown voltage |          | V <sub>(BR)DSS</sub> | $I_D$ = 10 mA, $V_{GS}$ = 0 V                     | 30  |      |     | V    |
| Drain-source breakdown voltage | (Note 1) | V <sub>(BR)DSX</sub> | $I_D$ = 10 mA, $V_{GS}$ = -20 V                   | 15  |      |     |      |
| Gate threshold voltage         | (Note 2) | $V_{th}$             | $V_{DS} = 10 \text{ V}, I_D = 0.1 \text{ mA}$     | 1.3 |      | 2.5 |      |
| Drain-source on-resistance     | (Note 3) | R <sub>DS(ON)</sub>  | $I_D = 2.0 \text{ A}, V_{GS} = 10 \text{ V}$      |     | 67   | 95  | mΩ   |
|                                |          |                      | $I_D = 1.0 \text{ A}, V_{GS} = 4.5 \text{ V}$     | _   | 100  | 140 |      |
| Forward transfer admittance    | (Note 3) | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 A    | 2.5 | 5    | _   | S    |

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (0.1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 3: Pulse measurement.

# 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V,                                     | _   | 126  |     | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> | f = 1 MHz  |     | 8    |     |      |
| Output capacitance             | Coss             |  | _   | 26   |     |      |
| Switching time (turn-on time)  | t <sub>on</sub>  | $V_{DD}$ = 15 V, $I_{D}$ = 0.5 A<br>$V_{GS}$ = 0 to 4.5 V, $R_{G}$ = 10 $\Omega$ , |     | 7    |     | ns   |
| Switching time (turn-off time) | t <sub>off</sub> | Duty $\leq$ 1%, Input: $t_r$ , $t_f$ < 5 ns<br>Common source, See Chapter 5.3      | _   | 8    |     |      |

#### 5.3. Switching Time Test Circuit

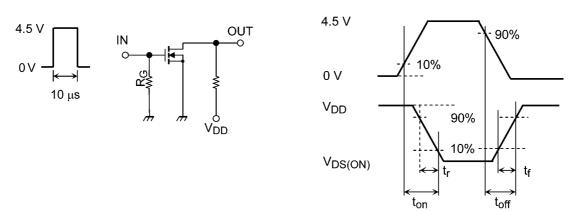


Fig. 5.3.1 Test Circuit of Switching Time

Fig. 5.3.2 Input Waveform/Output Waveform

## 5.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25°C)

| Characteristics                                 | Symbol           | Test Condition                                  | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | V <sub>DD</sub> = 15 V, V <sub>GS</sub> = 4.5V, | _   | 1.7  | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> | $I_D = 3.0 \text{ A}$                           | _   | 0.8  | _   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |   | _   | 0.7  | _   |      |



# 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25^{\circ}C$ )

| Characteristics       |          | Symbol    | Test Condition                               | Min | Тур.  | Max  | Unit |
|-----------------------|----------|-----------|--|-----|-------|------|------|
| Diode forward voltage | (Note 1) | $V_{DSF}$ | $I_D = -3.0 \text{ A}, V_{GS} = 0 \text{ V}$ | _   | -0.89 | -1.2 | V    |

Note 1: Pulse measurement.

## 6. Marking

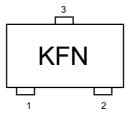


Fig. 6.1 Marking

### 7. Characteristics Curves (Note)

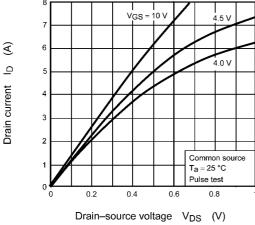
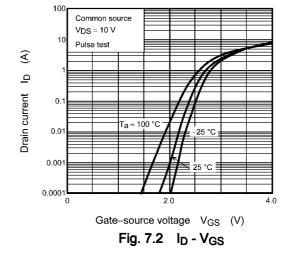


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>



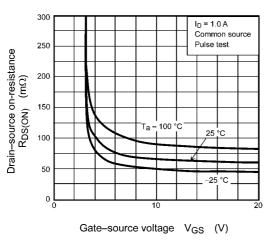


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

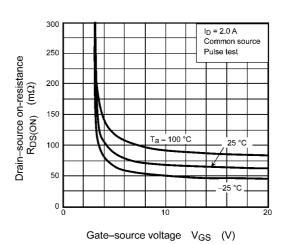


Fig. 7.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

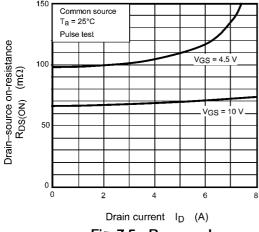


Fig. 7.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

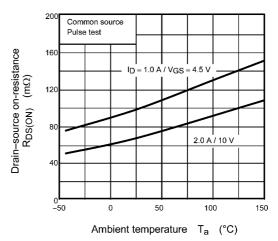


Fig. 7.6  $R_{DS(ON)}$  -  $T_a$ 

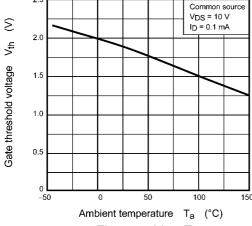


Fig. 7.7 V<sub>th</sub> - T<sub>a</sub>

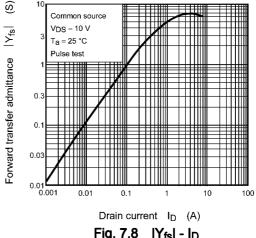


Fig. 7.8 |Y<sub>fs</sub>| - I<sub>D</sub>

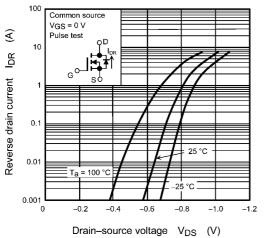


Fig. 7.9  $I_{DR}$  -  $V_{DS}$ 

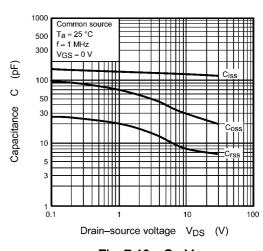


Fig. 7.10 C - V<sub>DS</sub>

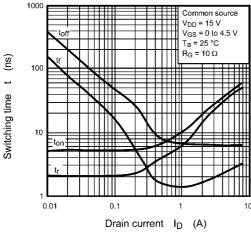


Fig. 7.11 t - ID

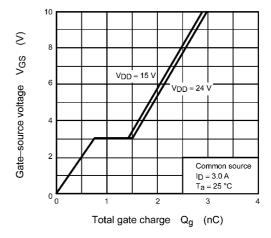
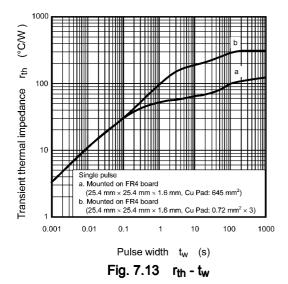


Fig. 7.12 Dynamic Input/Output Characteristics



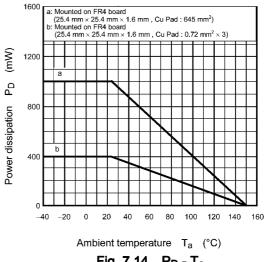


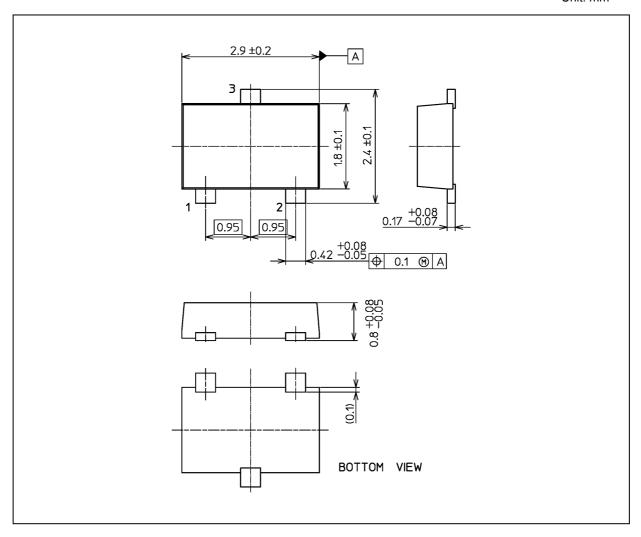
Fig. 7.14 P<sub>D</sub> - T<sub>a</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

|                   | Package Name(s) |
|-------------------|-----------------|
| TOSHIBA: 2-3Z1S   |                 |
| Nickname: SOT-23F |                 |

Rev.2.0



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